60V NPN LOW SATURATION MEDIUM POWER TRANSISTOR IN E-LINE

SUMMARY

 $BV_{CEO} = 60V : R_{SAT} = 34m\Omega; I_C = 4.5A$

DESCRIPTION

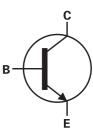
Packaged in the E-line outline this new low saturation 60V NPN transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.

FEATURES

- Externely low equivalent on-resistance; $R_{SAT} = 34m\Omega$ at 5A
- 4.5 amps continuous current
- Up to 15 amps peak current
- Very low saturation voltages

APPLICATIONS

- Emergency lighting circuits
- Motor driving (including DC fans)
- Solenoid, relay and actuator drivers
- DC modules
- Backlight inverters



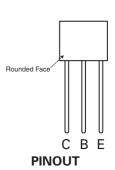
E-LINE

ORDERING INFORMATION

DEVICE	QUANTITY
ZXTN2010ASTOA	2000 units / reel
ZXTN2010ASTZ	2000 units / carton

DEVICE MARKING

2X I N20 10





ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Collector-base voltage	BV _{CBO}	150	V
Collector-emitter voltage	BV _{CEO}	60	V
Emitter-base voltage	BV _{EBO}	7	V
Continuous collector current (a)	I _C	4.5	А
Peak pulse current	I _{CM}	15	А
Practical power dissipation (a)	P _D	1.0	W
Linear derating factor		8	mW/°C
Power dissipation at T _A =25°C (b)	P _D	0.71	W
Linear derating factor		5.7	mW/°C
Operating and storage temperature range	T _j , T _{stg}	-55 to +150	°C

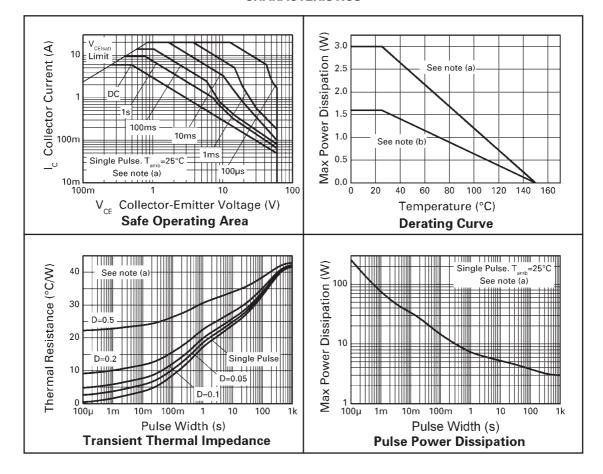
THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to ambient ^(a)	$R_{\Theta JA}$	125	°C/W
Junction to ambient ^(b)	$R_{\Theta JA}$	175	°C/W



 ⁽a) For a device through hole mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions. Collector lead length to solder point 4mm.
 (b) For a device mounted in a socket in still air conditions. Collector lead length 10mm.

CHARACTERISTICS





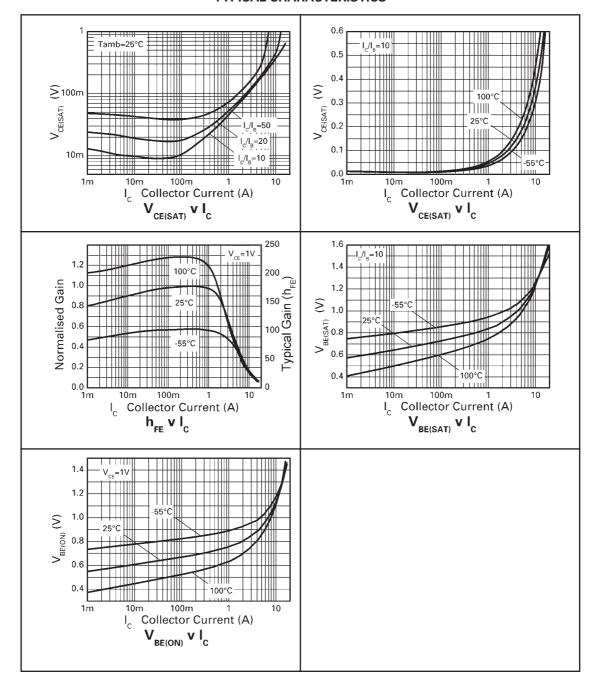
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Collector-base breakdown voltage	BV _{CBO}	150	190		V	I _C =100μA
Collector-emitter breakdown voltage	BV _{CER}	150	190		V	I_C =1μA, RB≤1k Ω
Collector-emitter breakdown voltage	BV _{CEO}	60	80		V	I _C =10mA*
Emitter-base breakdown voltage	BV _{EBO}	7	8.1		V	I _E =100μA
Collector cut-off current	I _{CBO}			50	nA	V _{CB} =120V
				0.5	μΑ	V _{CB} =120V, T _{amb} =100°C
Collector cut-off current	I _{CER}			100	nA	V _{CB} =120V
	R≤1kΩ			0.5	μΑ	V _{CB} =120V, T _{amb} =100°C
Emitter cut-off current	I _{EBO}			10	nA	V _{EB} =6V
Collector-emitter saturation voltage	V _{CE(SAT)}		18	30	mV	I _C =100mA, I _B =5mA*
			40	55	mV	I _C =1A, I _B =100mA*
			45	65	mV	I _C =1A, I _B =50mA*
			95	130	mV	I _C =2A, I _B =50mA*
			170	210	mV	I _C =5A, I _B =200mA*
Base-emitter saturation voltage	V _{BE(SAT)}		950	1050	mV	I _C =4A, I _B =200mA*
Base-emitter turn-on voltage	V _{BE(ON)}		840	950	mV	I _C =4A, V _{CE} =1V*
Static forward current transfer ratio	h _{FE}	100	200			I _C =10mA, V _{CE} =1V*
		100	200	300		I _C =2A, V _{CE} =1V*
		55	105			I _C =5A, V _{CE} =1V*
		20	40			I _C =10A, V _{CE} =1V*
Transition frequency	f _T		130		MHz	I _C =100mA, V _{CE} =10V
						f=50MHz
Output capacitance	СОВО		31		pF	V _{CB} =10V, f=1MHz*
Switching times	t _{ON}		42		ns	I _C =1A, V _{CC} =10V,
	t _{OFF}		760		ns	I _{B1} =I _{B2} =100mA

^{*} Measured under pulsed conditions. Pulse width $\leq 300 \mu s;$ duty cycle $\leq 2\%.$



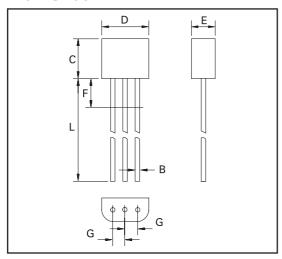
TYPICAL CHARACTERISTICS



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PACKAGE OUTLINE



Controlling dimensions are in millimeters. Approximate conversions are given in inches

PACKAGE DIMENSIONS

DIM	Millin	neters	Inches		
DIIVI	Min	Max	Min	Max	
Α	0.41	0.495	0.016	0.0195	
В	0.41	0.495	0.016	0.0195	
С	3.61	4.01	0.142	0.158	
D	4.37	4.77	0.172	0.188	
Е	2.16	2.41	0.085	0.095	
F	_	2.50	_	0.098	
G	1.27 NOM		0.050	NOM	
L	13.00	13.97	0.512	0.550	

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